

80V N-Channel MOSFET

Product Summary

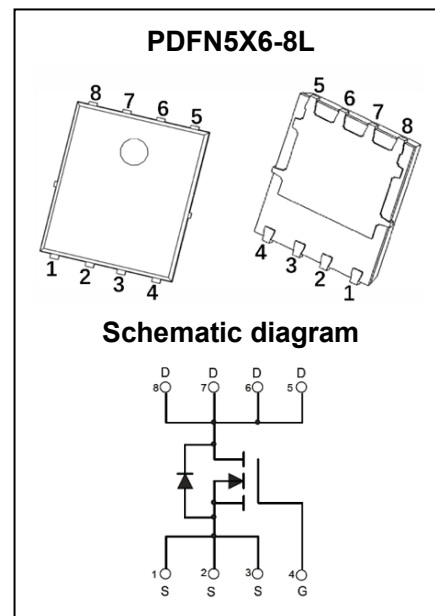
$V_{(BR)DSS}$	$R_{DS(on)TYP}$	I_D
80V	2.0m Ω @10V	175A
	2.5m Ω @6.0V	

Feature

- Split Gate Trench Technology
- Low $R_{DS(ON)}$
- Low Gate Charge
- Low Gate Resistance
- 100% UIS Tested

Application

- Power Management
- Load Switching
- Motor Driving
- High frequency switching, synchronous rectification



Package Marking and Ordering Information

Part Number	Package	Marking	Packing	Reel Size	Tape Width	Qty
T022N08NNCU	PDFN5X6-8L	T022N08N	Reel & Tape	330mm	12mm	5000pcs

ABSOLUTE MAXIMUM RATINGS ($T_A = 25^\circ\text{C}$ unless otherwise noted)

Parameter	Symbol	Value	Unit
Drain-Source Voltage	V_{DS}	80	V
Gate-Source Voltage	V_{GS}	± 20	V
Continuous Drain Current ¹	I_D	$T_C = 25^\circ\text{C}$	175
		$T_C = 100^\circ\text{C}$	110
Pulsed Drain Current ²	I_{DM}	700	A
Single Pulsed Avalanche Current ³	I_{AS}	60	A
Single Pulsed Avalanche Energy ³	E_{AS}	900	mJ
Power Dissipation ⁵	P_D	125	W
Thermal Resistance from Junction to Ambient ⁶	$R_{\theta JA}$	50	$^\circ\text{C/W}$
Thermal Resistance from Junction to Case	$R_{\theta JC}$	1.0	$^\circ\text{C/W}$
Junction Temperature	T_J	150	$^\circ\text{C}$
Storage Temperature	T_{STG}	-55~ +150	$^\circ\text{C}$

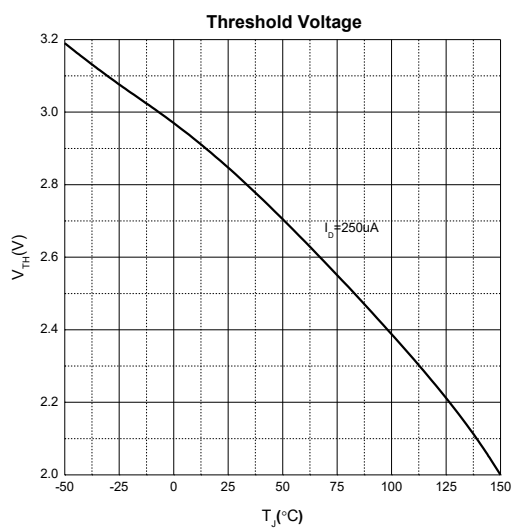
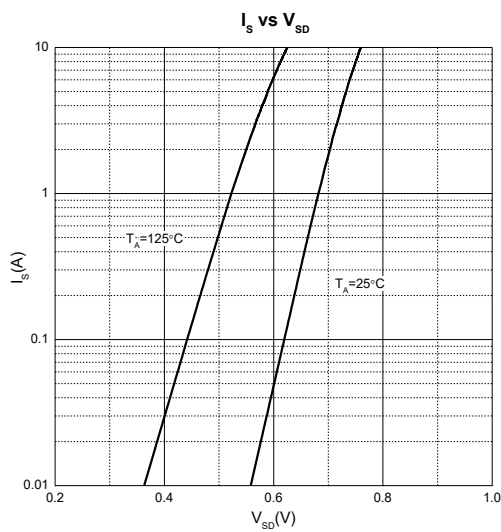
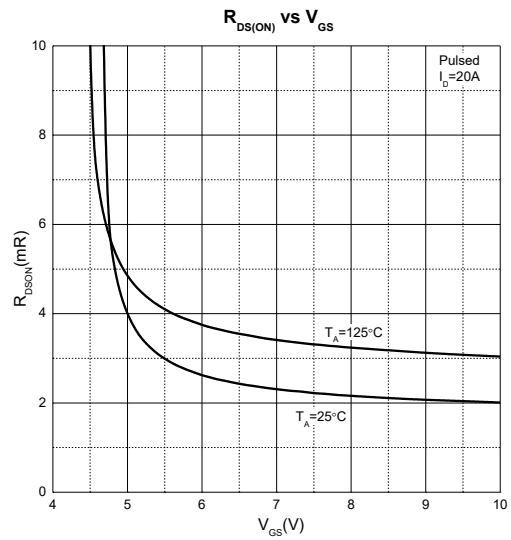
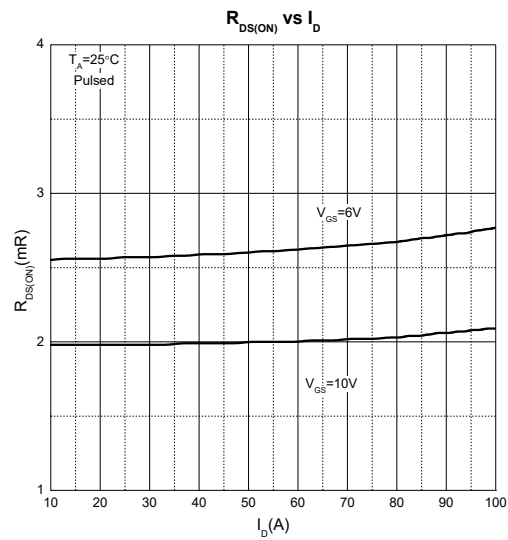
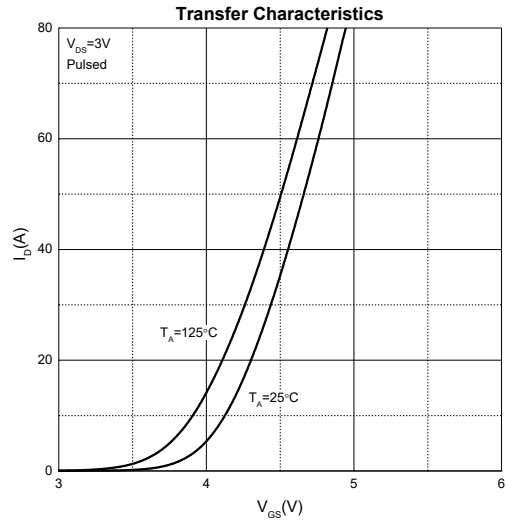
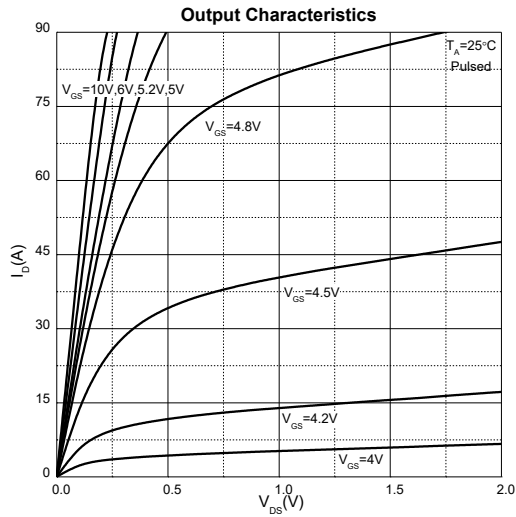
Electrical Characteristics ($T_A=25^\circ\text{C}$ unless otherwise noted)

Parameter	Symbol	Test Condition	Min	Type	Max	Unit
Off Characteristics						
Drain-Source Breakdown Voltage	$V_{(BR)DSS}$	$V_{GS} = 0V, I_D = 250\mu A$	80			V
Zero Gate Voltage Drain Current	I_{DSS}	$V_{DS} = 80V, V_{GS} = 0V$			1	μA
Gate-Body Leakage Current	I_{GSS}	$V_{GS} = \pm 20V, V_{DS} = 0V$			± 100	nA
On Characteristics⁴						
Gate Threshold Voltage	$V_{GS(th)}$	$V_{DS} = V_{GS}, I_D = 250\mu A$	2.0	3.0	4.0	V
Drain-Source On-Resistance	$R_{DS(on)}$	$V_{GS} = 10V, I_D = 20A$		2.0	2.5	$m\Omega$
		$V_{GS} = 6.0V, I_D = 15A$		2.5	3.8	$m\Omega$
Forward Transconductance	g_{FS}	$V_{DS} = 5V, I_D = 20A$	50			S
Dynamic Characteristics						
Input Capacitance	C_{iss}	$V_{DS} = 40V, V_{GS} = 0V, f = 1MHz$		5487		pF
Output Capacitance	C_{oss}			1000		
Reverse Transfer Capacitance	C_{rss}			108		
Gate Resistance	R_g	$V_{DS} = 0V, V_{GS} = 0V, f = 1MHz$		2.0		Ω
Switching Characteristics						
Total Gate Charge	Q_g	$V_{DS} = 40V, V_{GS} = 10V, I_D = 50A$		80		nC
Gate-Source Charge	Q_{gs}			23		
Gate-Drain Charge	Q_{gd}			19		
Gate Plateau Voltage	$V_{plateau}$			4.5		V
Turn-On Delay Time	$t_{d(on)}$	$V_{DD} = 40V, V_{GS} = 10V, I_D = 20A,$ $R_G = 3\Omega$		10		ns
Turn-On Rise Time	t_r			20		
Turn-Off Delay Time	$t_{d(off)}$			25		
Turn-Off Fall Time	t_f			15		
Source-Drain Diode Characteristics						
Diode Forward Voltage ⁴	V_{SD}	$V_{GS} = 0V, I_S = 20A$			1.2	V
Diode Continuous Forward Current ¹	I_S	$T_C = 25^\circ\text{C}$			175	A
Diode Pulse Forward Current ²	I_{SM}	$T_C = 25^\circ\text{C}$			700	A
Diode Reverse Recovery Time	t_{rr}	$I_F = 20A, di/dt = 100A/\mu s$		70		ns
Diode Reverse Recovery Charge	Q_{rr}	$I_F = 20A, di/dt = 100A/\mu s$		100		nC

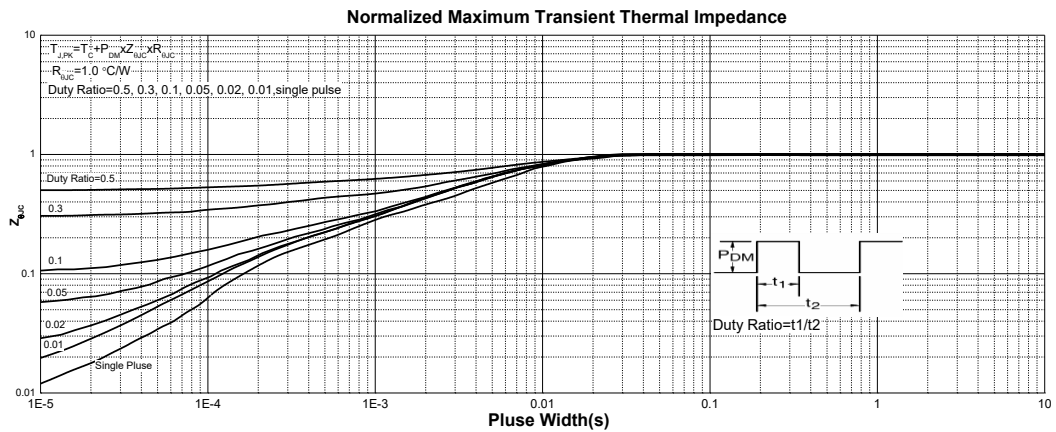
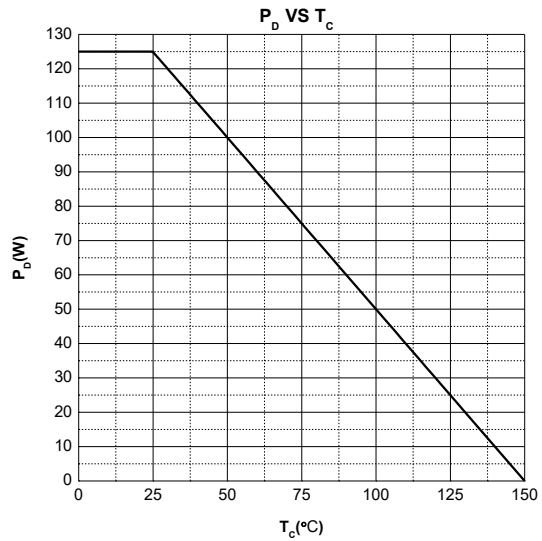
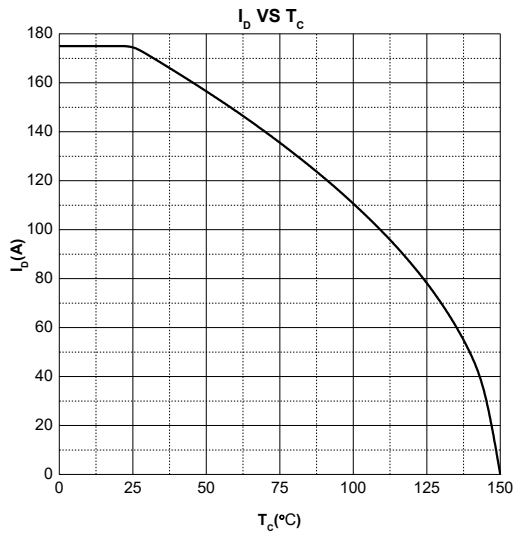
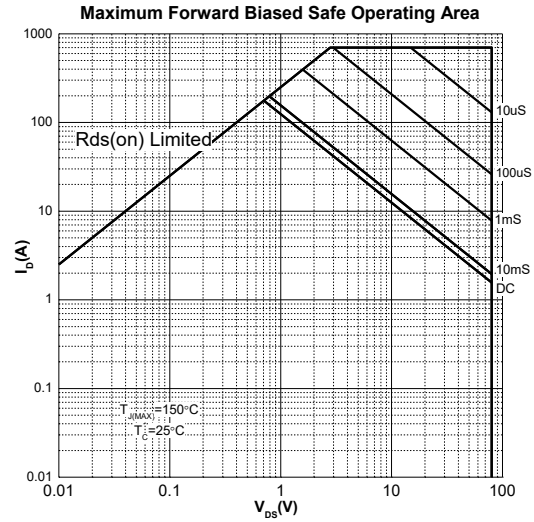
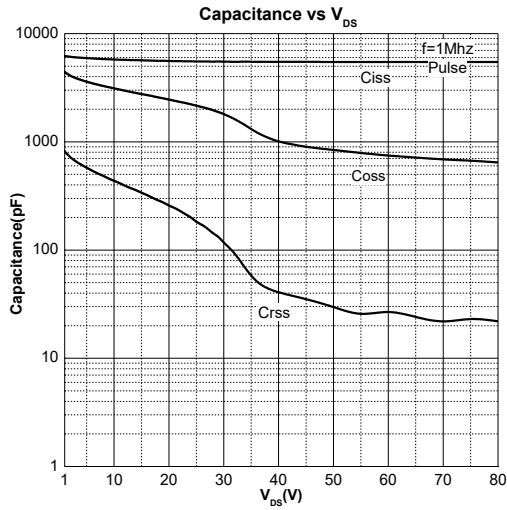
Notes:

- 1.The maximum current rating is limited by package. And device mounted on a large heatsink.
- 2.Pulse Test: Pulse Width $\leq 10\mu s$, duty cycle $\leq 1\%$.
- 3.EAS condition: $V_{DD} = 40V, V_{GS} = 10V, L = 0.5mH, R_G = 25\Omega$ Starting $T_J = 25^\circ\text{C}$.
- 4.Pulse Test: Pulse Width $\leq 300\mu s$, duty cycle $\leq 2\%$.
- 5.The power dissipation P_D is limited by $T_{J(MAX)} = 150^\circ\text{C}$. And device mounted on a large heatsink.
- 6.Device mounted on $1in^2$ FR-4 board with 2oz. Copper, in a still air environment with $T_A = 25^\circ\text{C}$.

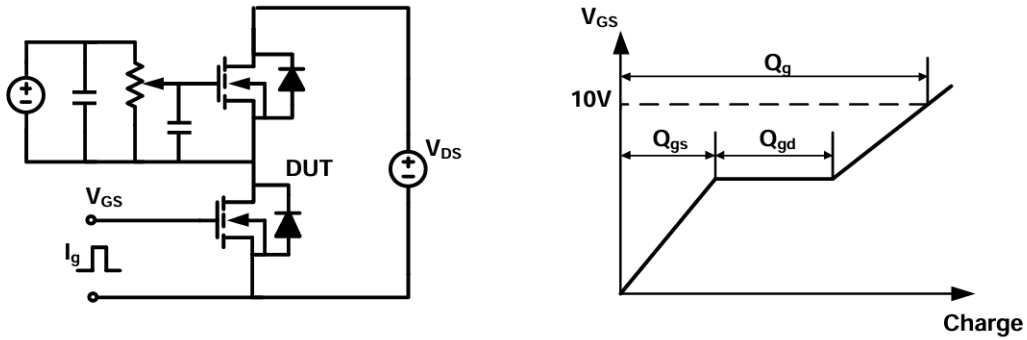
Typical Characteristics



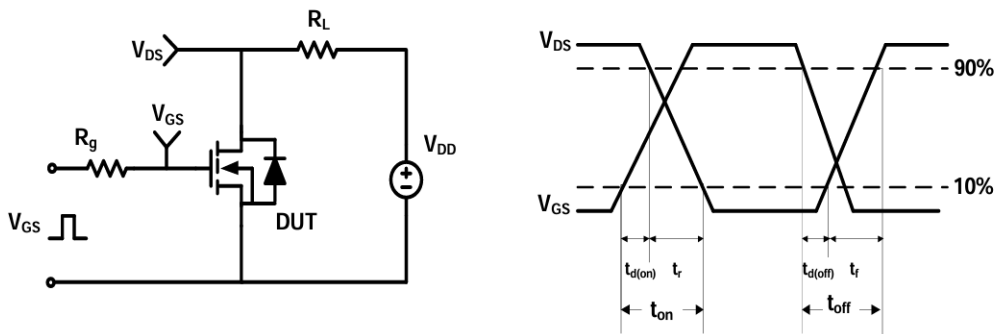
Typical Characteristics



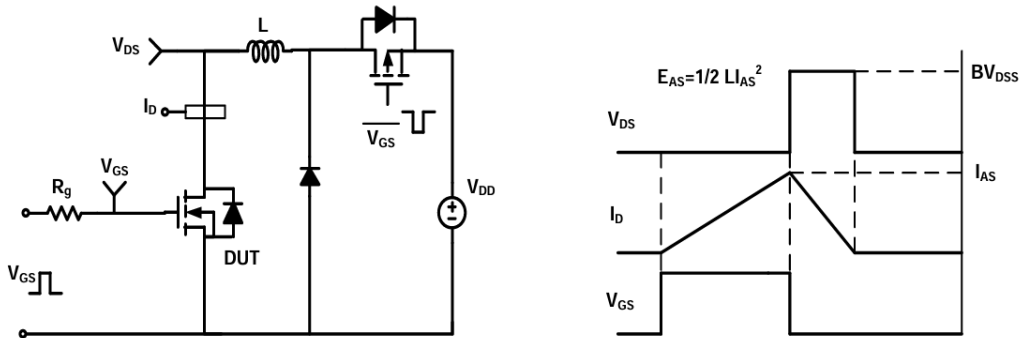
Gate Charge Test Circuit & Waveform



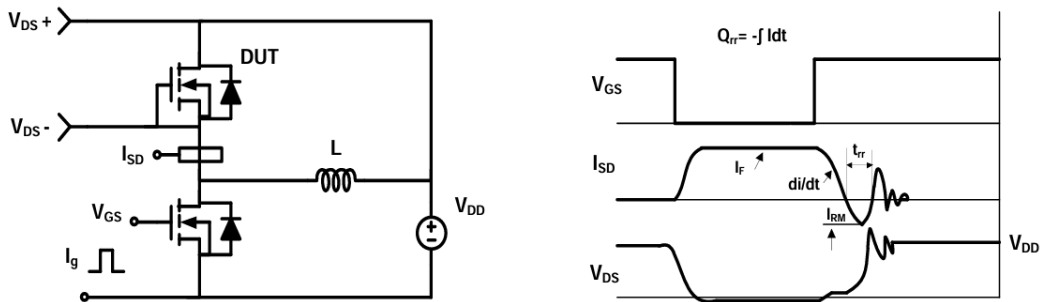
Resistive Switching Test Circuit & Waveform

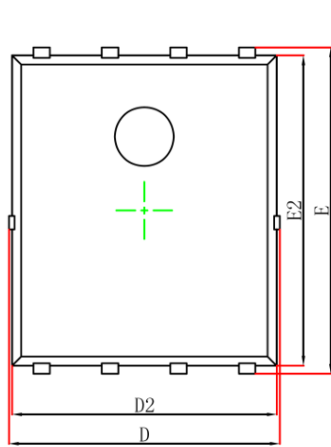


Unclamped Inductive Switching (UIS) Test Circuit & Waveform

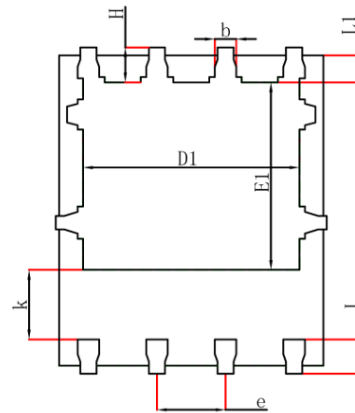


Diode Recovery Test Circuit & Waveform

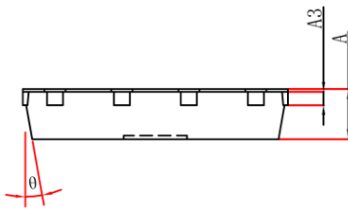




Top View
[顶视图]



Bottom View
[背视图]



Side View
[侧视图]

Symbol	Dimensions In Millimeters		Dimensions In Inches	
	Min.	Max.	Min.	Max.
A	0.900	1.10	0.035	0.043
A3	0.254REF		0.010REF	
D	4.700	5.260	0.185	0.207
E	5.750	6.250	0.226	0.246
D1	3.560	4.500	0.140	0.177
E1	3.180	3.660	0.125	0.144
D2	4.700	5.100	0.185	0.201
E2	5.600	6.000	0.220	0.236
k	1.100	-	0.043	-
b	0.300	0.500	0.012	0.020
e	1.270TYP		0.050TYP	
L	0.510	0.710	0.020	0.028
L1	0.424	0.576	0.017	0.023
H	0.510	0.710	0.020	0.028
θ	8°	12°	8°	12°